



TEF6621

Tuner on main-board IC

Rev. 01.04 — 7 August 2008

Objective data sheet

1. General description

The TEF6621 is an AM/FM radio including Phase-Locked Loop (PLL) tuning system. The system is designed in such a way, that it can be used as a world-wide tuner covering common FM and AM bands for radio reception. All functions are controlled by the I²C-bus. Besides the basic feature set it provides a good weak signal processing function.

2. Features

- FM tuner for Japan, Europe and US reception
- AM tuner for Long Wave (LW) and Medium Wave (MW) reception
- Integrated AM Radio Frequency (RF) selectivity
- Integrated PLL tuning system; controlled via I²C-bus
- Fully integrated Local Oscillator (LO)
- No alignment needed
- Very easy application on the main board
- No critical RF components
- Fully integrated Intermediate Frequency (IF) filters and FM stereo decoder
- Fully integrated FM noise blanker
- Field strength (LEVEL), multipath [Wideband AM (WAM)] and noise [UltraSonic Noise (USN)] dependent stereo blend
- Field strength (LEVEL), multipath (WAM) and noise (USN) dependent High-Cut Control (HCC)
- Field strength (LEVEL), multipath (WAM) and noise (USN) dependent soft mute
- Single power supply

3. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage	on pins V _{CC1} and V _{CC2}	8	8.5	9	V
I _{CC}	supply current	into pins V _{CC1} , V _{CC2} and VREGSUP				
		FM	90	120	140	mA
		AM	100	134	150	mA
FM path						
f _{RF}	RF frequency	FM tuning range	76	-	108	MHz
V _{i(sens)}	input sensitivity voltage	(S+N)/N = 26 dB; including weak signal handling	-	5	-	dBμV
(S+N)/N	signal plus noise-to-noise ratio	V _{i(RF)} = 1 mV; Δf = 22.5 kHz	55	60	-	dB
THD	total harmonic distortion	mono; Δf = 75 kHz; V _{i(RF)} = 1 mV	-	0.4	0.8	%
α _{image}	image rejection	f _{RF(image)} = f _{RF(wanted)} ± 2 × f _{IF}	45	60	-	dB
α _{cs}	channel separation	V _{i(RF)} = 1 mV; data byte Fh bits CHSEP[2:0] = 100	26	40	-	dB
AM path						
f _{RF}	RF frequency	AM (LW) tuning range	144	-	288	kHz
		AM (MW) tuning range	522	-	1710	kHz
V _{i(sens)}	input sensitivity voltage	S/N = 26 dB; data byte 3h bits DEMP[1:0] = 10				
		MW	-	34	-	dBμV
		LW	-	40	-	dBμV
(S+N)/N	signal plus noise-to-noise ratio	V _{i(RF)} = 10 mV	50	56	-	dB
THD	total harmonic distortion	V _{i(RF)} = 1 mV; m = 80 %	-	0.7	1	%
α _{image}	image rejection	f _{RF(image)} = f _{RF(wanted)} ± 2 × f _{IF}	40	55	-	dB

4. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
TEF6621T	SO32	plastic small outline package; 32 leads; body width 7.5 mm	SOT287-1

5. Block diagram

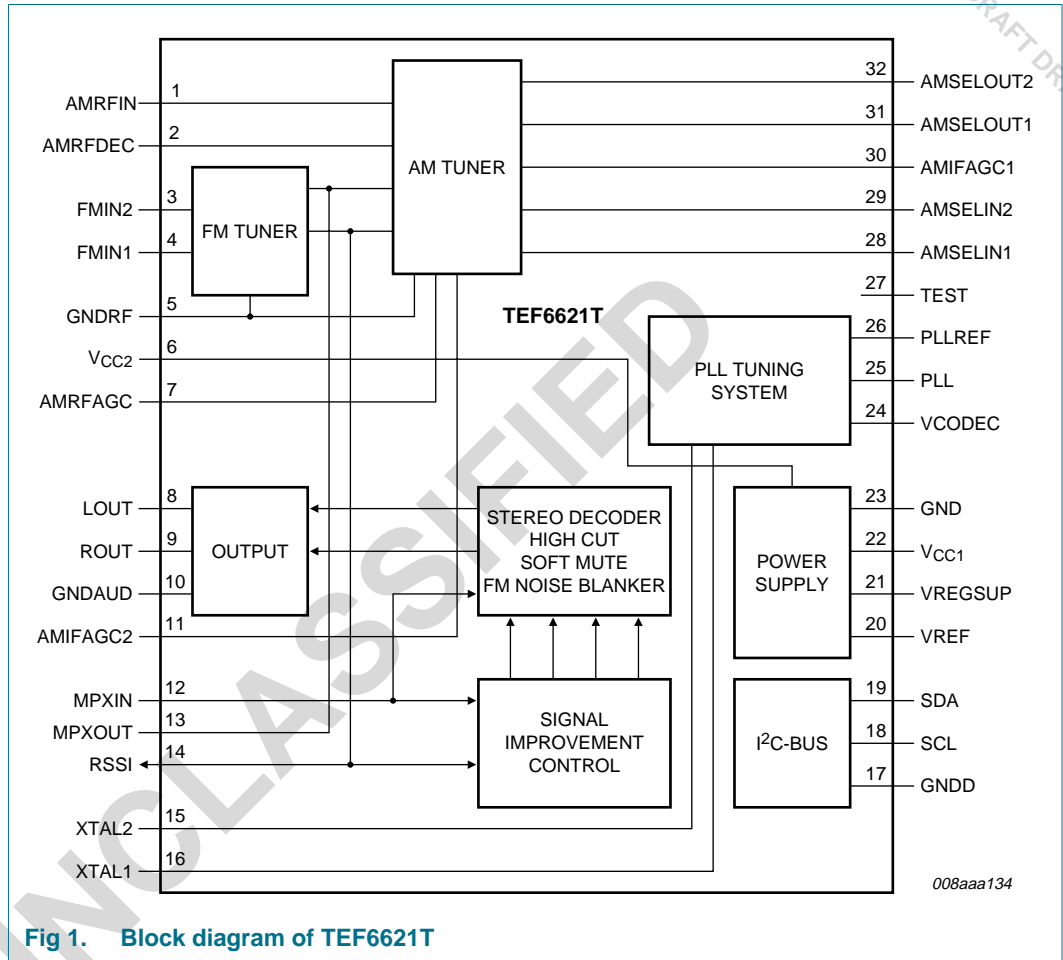


Fig 1. Block diagram of TEF6621T

6. Pinning information

6.1 Pinning

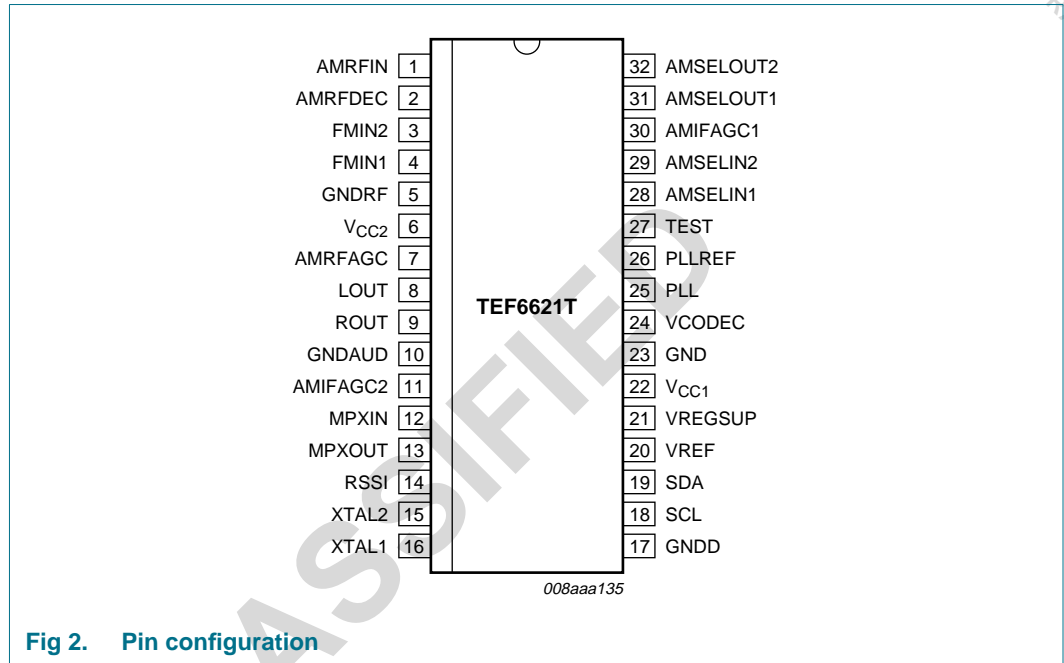


Fig 2. Pin configuration

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
AMRFIN	1	AM RF single-ended input
AMRFDEC	2	AM RF decoupling
FMIN2	3	FM RF differential input 2
FMIN1	4	FM RF differential input 1
GNDRF	5	RF ground
V _{CC2}	6	supply voltage 2
AMRFAGC	7	AM RF Automatic Gain Control (AGC)
LOUT	8	audio left output
ROUT	9	audio right output
GNDAUD	10	audio ground
AMIFAGC2	11	AM IF AGC 2
MPXIN	12	FM Multiplex (MPX) and AM audio input to stereo decoder
MPXOUT	13	FM MPX and AM audio output from tuner part
RSSI	14	Received Signal Strength Indication (RSSI)
XTAL2	15	4 MHz crystal oscillator pin 2
XTAL1	16	4 MHz crystal oscillator pin 1
GNDD	17	digital ground
SCL	18	I ² C-bus clock input

Table 3. Pin description ...continued

Symbol	Pin	Description
SDA	19	I ² C-bus data input and output
VREF	20	reference voltage decoupling
VREGSUP	21	supply voltage internal voltage regulators
V _{CC1}	22	supply voltage 1
GND	23	ground
VCODEC	24	decoupling for Voltage-Controlled Oscillator (VCO) supply voltage
PLL	25	PLL tuning voltage
PLLREF	26	PLL reference voltage
TEST	27	test pin; leave open in normal operation
AMSELIN1	28	AM selectivity input 1
AMSELIN2	29	AM selectivity input 2
AMIFAGC1	30	AM IF AGC 1
AMSELOUT1	31	AM selectivity output 1
AMSELOUT2	32	AM selectivity output 2

7. Functional description

7.1 FM tuner

The RF input signal is mixed to a low IF with inherent image suppression. The IF signal is filtered and demodulated. The complete signal path is fully integrated.

7.2 AM tuner

The RF signal is filtered and mixed to a low IF with inherent image suppression. The IF signals are filtered and demodulated. The signal path is highly integrated.

7.3 PLL tuning system

The PLL tuning system includes a fully integrated VCO. To avoid problems with unwanted signals on image side, the receiver controls automatically high-side or low-side injection.

7.4 FM stereo decoder

The MPX signal from the FM tuner is translated by the stereo decoder into a left and right audio channel. Good channel separation is achieved without alignment.

7.5 Weak signal processing and noise blanker

The reception quality of the station received is measured by a combination of detectors: field strength (LEVEL), multipath (WAM) and noise (USN). The audio processing functions soft mute, HCC and stereo blend are controlled accordingly to maintain the best possible audio quality in case of poor signal conditions. Audio disturbances like e.g. ignition noise are suppressed by the noise blanker circuit, using USN detection on MPX and spike detection on the level signal.

9. Limiting values

Table 57. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage	on pins V_{CC1} and V_{CC2}	-0.3	+10	V
ΔV_{CCn}	voltage difference between any supply pins	between pins V_{CC1} and V_{CC2}	-0.3	+0.3	V
V_{SCL}	voltage on pin SCL		-0.3	+6	V
V_{SDA}	voltage on pin SDA		-0.3	+6	V
$V_{AMRFDEC}$	voltage on pin AMRFDEC		-0.3	+6	V
V_{AMRFIN}	voltage on pin AMRFIN		-0.3	+6	V
$V_{AMRFAGC}$	voltage on pin AMRFAGC		-0.3	+6	V
$V_{AMIFAGC2}$	voltage on pin AMIFAGC2		-0.3	+6	V
V_{RSSI}	RSSI voltage		-0.3	+6	V
V_{VCODEC}	voltage on pin VCODEC		-0.3	+6	V
V_{PLL}	voltage on pin PLL		-0.3	+6	V
V_{PLLREF}	voltage on pin PLLREF		-0.3	+6	V
V_{TEST}	voltage on pin TEST		-0.3	+6	V
$V_{AMIFAGC1}$	voltage on pin AMIFAGC1		-0.3	+6	V
V_{VREF}	voltage on pin VREF		-0.3	+6	V
V_n	voltage on any other pin		-0.3	+ V_{CC}	V
T_{stg}	storage temperature		-40	+150	°C
T_{amb}	ambient temperature		-20	+85	°C
T_j	junction temperature		-	150	°C
V_{esd}	electrostatic discharge voltage	human body model	[1] -2000	+2000	V
		machine model	[2] -200	+200	V

[1] Class 2 according to JESD22-A114.

[2] Class B according to EIA/JESD22-A115.

10. Thermal characteristics

Table 58. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; single layer board with a copper thickness of 35 μm ; see Figure 28	[1] 48	K/W
Ψ_{j-top}	thermal characterization parameter from junction to top of package		4.5	K/W

[1] The thermal resistance depends strongly on the PCB design. An application different to [Figure 28](#) must ensure that the thermal resistance is below 54 K/W to avoid violation of the maximum junction temperature; see [Table 57](#).

11. Static characteristics

Table 59. Static characteristics

$V_{CC} = 8.5\text{ V}$; $T_{amb} = 25\text{ °C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage	on pins V_{CC1} and V_{CC2}	8	8.5	9	V
I_{CC}	supply current	into pins V_{CC1} , V_{CC2} and VREGSUP				
		FM	90	120	140	mA
		AM	100	134	150	mA
$V_{VREGSUP}$	voltage on pin VREGSUP	$T_{amb} = -20\text{ °C}$ to $+85\text{ °C}$	6.35	-	-	V
Power-on reset						
$V_{P(POR)}$	power-on reset supply voltage	reset at power-on	6.5	6.75	7.0	V
$V_{hys(POR)}$	power-on reset hysteresis voltage		-	0.2	-	V
t_{start}	start time	series resistance of crystal $R_s = 150\ \Omega$	-	10	100	ms
Logic pins SDA and SCL (voltage referenced to pin GNDD)						
V_{IH}	HIGH-level input voltage		[1] 1.58	-	5.5	V
V_{IL}	LOW-level input voltage		[1] -0.5	-	+1.04	V

- [1] SDA and SCL HIGH and LOW internal thresholds are specified according to an I²C-bus voltage of $2.5\text{ V} \pm 10\%$ or $3.3\text{ V} \pm 5\%$. The I²C-bus interface tolerates also SDA and SCL signals from a 5 V I²C-bus, but does not fulfill the 5 V I²C-bus specification completely. The TEF6621 complies with the fast-mode I²C-bus protocol. The maximum I²C-bus communication speed is 400 kbit/s.

12. Dynamic characteristics

Table 60. Dynamic characteristics

$V_{CC} = 8.5\text{ V}$; $T_{amb} = 25\text{ °C}$; unless otherwise specified.

FM condition: all RF voltages refer to an unterminated RMS voltage with a source impedance $75\ \Omega$; $f_{mod} = 1\text{ kHz}$,

$\Delta f = 22.5\text{ kHz}$, de-emphasis = $50\ \mu\text{s}$, $f_{RF} = 97.1\text{ MHz}$; unless otherwise specified.

AM condition: all RF voltages are RMS values measured at the input of a $15\text{ pF}/60\text{ pF}$ dummy aerial; $f_{mod} = 400\text{ Hz}$,

$m = 30\%$, $f_{RF} = 990\text{ kHz}$; unless otherwise specified.

All values measured in a test circuit according to [Figure 29](#); default settings; audio signals measured at LOUT and ROUT with IEC tuner filter (200 Hz to 15 kHz; IEC 60315-4); unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Crystal oscillator; pins XTAL1 and XTAL2						
f_{xtal}	crystal frequency	fundamental frequency	-	4	-	MHz
$\Delta f_{xtal}/f_{xtal}$	relative crystal frequency variation	device inaccuracy	-45	-	+45	10^{-6}
C_i	input capacitance	input capacitance from pin XTAL1 and pin XTAL2 to ground	1	3	4	pF
R_i	input resistance		-	-	-750	Ω

Table 60. Dynamic characteristics ...continued

$V_{CC} = 8.5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

FM condition: all RF voltages refer to an unterminated RMS voltage with a source impedance $75\text{ }\Omega$; $f_{mod} = 1\text{ kHz}$, $\Delta f = 22.5\text{ kHz}$, de-emphasis = $50\text{ }\mu\text{s}$, $f_{RF} = 97.1\text{ MHz}$; unless otherwise specified.

AM condition: all RF voltages are RMS values measured at the input of a $15\text{ pF}/60\text{ pF}$ dummy aerial; $f_{mod} = 400\text{ Hz}$, $m = 30\%$, $f_{RF} = 990\text{ kHz}$; unless otherwise specified.

All values measured in a test circuit according to [Figure 29](#); default settings; audio signals measured at LOUT and ROUT with IEC tuner filter (200 Hz to 15 kHz; IEC 60315-4); unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Tuning system						
C/N_{LO}	LO carrier-to-noise ratio	$f_{LO} = 100\text{ MHz}$; $\Delta f = 10\text{ kHz}$	-	98	-	$\text{dBc}/\sqrt{\text{Hz}}$
t_{tune}	tuning time	FM (Europe/USA/Japan) $f_{RF} = 87.5\text{ MHz}$ to 108 MHz	-	1.8	-	ms
		AM (MW) $f_{RF} = 0.53\text{ MHz}$ to 1.7 MHz	-	9	-	ms
		AM (LW) $f_{RF} = 0.144\text{ MHz}$ to 0.288 MHz	-	3.5	-	ms
f_{RF}	RF frequency	FM tuning range	76	-	108	MHz
		AM (LW) tuning range	144	-	288	kHz
		AM (MW) tuning range	522	-	1710	kHz
$f_{\text{tune(step)}}$	step of tuning frequency	FM (Europe/USA/Japan)	-	50	-	kHz
		AM (LW and MW)	-	1	-	kHz
FM path						
$V_{i(\text{sens})}$	input sensitivity voltage	(S+N)/N = 26 dB; without weak signal handling	-	5.5	-	$\text{dB}\mu\text{V}$
		(S+N)/N = 26 dB; including weak signal handling	-	5	-	$\text{dB}\mu\text{V}$
		(S+N)/N = 46 dB; including weak signal handling	-	16	-	$\text{dB}\mu\text{V}$
NF	noise figure		-	6	9	dB
(S+N)/N	signal plus noise-to-noise ratio	$V_{i(\text{RF})} = 1\text{ mV}$; $\Delta f = 22.5\text{ kHz}$	55	60	-	dB
α_{ripple}	ripple rejection	$V_{\text{ripple}} / V_{\text{audio}}$; $V_{\text{ripple}} = 100\text{ mV}$; $f_{\text{ripple}} = 100\text{ Hz}$	34	44	-	dB
f_{IF}	IF frequency		-	150	-	kHz
α_{image}	image rejection	$f_{\text{RF(image)}} = f_{\text{RF(wanted)}} \pm 2 \times f_{IF}$	45	60	-	dB
IP3	third-order intercept point	$f_{\text{RF(unw)1}} = 97.5\text{ MHz}$; $f_{\text{RF(unw)2}} = 97.9\text{ MHz}$; $V_{i(\text{RF})} = 80\text{ dB}\mu\text{V}$	106	113	-	$\text{dB}\mu\text{V}$
S_{dyn}	dynamic selectivity	$V_{i(\text{RF})} = 10\text{ }\mu\text{V}$; $\Delta f_{\text{RF(unw)}} = 22.5\text{ kHz}$; (S+N)/N = 26 dB; mono; $f_{AF} = 1\text{ kHz}$				
		$\Delta f_{\text{RF}} = 100\text{ kHz}$	-	3	-	dB
		$\Delta f_{\text{RF}} = 200\text{ kHz}$	-	55	-	dB
S_{stat}	static selectivity	maximum IF bandwidth				
		$f_{i(\text{RF})} \pm 100\text{ kHz}$	10	14	25	dB
		$f_{i(\text{RF})} \pm 200\text{ kHz}$	54	64	74	dB
		$f_{i(\text{RF})} \pm 300\text{ kHz}$ (excluding image)	65	75	90	dB
$\alpha_{\text{sup(AM)}}$	AM suppression	AM: $f_{AF} = 1\text{ kHz}$; $m = 30\%$				
		$V_{i(\text{RF})} = 0.05\text{ mV}$ to 20 mV	45	55	-	dB
		$V_{i(\text{RF})} = 20\text{ mV}$ to 500 mV	40	50	-	dB

Table 60. Dynamic characteristics ...continued

$V_{CC} = 8.5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

FM condition: all RF voltages refer to an unterminated RMS voltage with a source impedance $75\text{ }\Omega$; $f_{mod} = 1\text{ kHz}$,

$\Delta f = 22.5\text{ kHz}$, de-emphasis = $50\text{ }\mu\text{s}$, $f_{RF} = 97.1\text{ MHz}$; unless otherwise specified.

AM condition: all RF voltages are RMS values measured at the input of a $15\text{ pF}/60\text{ pF}$ dummy aerial; $f_{mod} = 400\text{ Hz}$,

$m = 30\%$, $f_{RF} = 990\text{ kHz}$; unless otherwise specified.

All values measured in a test circuit according to [Figure 29](#); default settings; audio signals measured at LOUT and ROUT with IEC tuner filter (200 Hz to 15 kHz; IEC 60315-4); unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
FM front-end; pins FMIN1 and FMIN2						
$R_{i(\text{dif})}$	differential input resistance	$f_{RF} = 97.1\text{ MHz}$; maximum gain	200	300	400	Ω
$C_{i(\text{dif})}$	differential input capacitance	$f_{RF} = 97.1\text{ MHz}$	-	4	7	pF
FM RF AGC						
$V_{\text{start(AGC)}}$	AGC start voltage	RF input voltage for first AGC step; $V_{i(\text{RF})}$ value, at which the RF gain decreases by 6 dB with increasing $V_{i(\text{RF})}$; data byte 2h				
		bits RFAGC[1:0] = 00	83	86	89	$\text{dB}\mu\text{V}$
		bits RFAGC[1:0] = 01	81	84	87	$\text{dB}\mu\text{V}$
		bits RFAGC[1:0] = 10	79	82	85	$\text{dB}\mu\text{V}$
		bits RFAGC[1:0] = 11	77	80	83	$\text{dB}\mu\text{V}$
$V_{i(\text{RF})\text{AGC(hys)}}$	hysteresis of AGC RF input voltage	hysteresis of AGC start	1	-	5	dB
FM IF AGC						
$V_{i(\text{RF})\text{AGC}}$	AGC RF input voltage	$V_{i(\text{RF})}$ value, at which the IF gain decreases by 6 dB with increasing $V_{i(\text{RF})}$; start of AGC; first step	71	76	81	$\text{dB}\mu\text{V}$
$V_{i(\text{RF})\text{AGC(hys)}}$	hysteresis of AGC RF input voltage	hysteresis of AGC start	1	-	6	dB
FM RSSI; pin RSSI						
V_{RSSI}	RSSI voltage	$V_{i(\text{RF})} = -20\text{ dB}\mu\text{V}$	0.6	0.8	1.0	V
		$V_{i(\text{RF})} = 20\text{ dB}\mu\text{V}$	1.6	1.9	2.2	V
		$V_{i(\text{RF})} = 40\text{ dB}\mu\text{V}$	2.5	2.9	3.3	V
$\Delta V_{\text{RSSI}}/\Delta L_{i(\text{RF})}$	RSSI voltage difference to RF input level difference ratio	between $V_{i(\text{RF})} = 20\text{ dB}\mu\text{V}$ and $V_{i(\text{RF})} = 40\text{ dB}\mu\text{V}$	45	50	55	mV/dB
FM IF counter						
$f_{\text{IFc(res)}}$	IF counter frequency resolution		-	5	-	kHz
FM demodulator; pin MPXOUT						
R_o	output resistance		-	-	100	Ω
R_L	load resistance		5	-	-	$\text{k}\Omega$
C_L	load capacitance		-	-	20	pF
Δf_{max}	maximum frequency deviation	THD = 3 %; $V_{i(\text{RF})} = 10\text{ mV}$	115	140	-	kHz
V_o	output voltage	$\Delta f = 22.5\text{ kHz}$; $f_{\text{AF}} = 1\text{ kHz}$	180	230	300	mV

Table 60. Dynamic characteristics ...continued

$V_{CC} = 8.5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

FM condition: all RF voltages refer to an unterminated RMS voltage with a source impedance $75\text{ }\Omega$; $f_{mod} = 1\text{ kHz}$, $\Delta f = 22.5\text{ kHz}$, de-emphasis = $50\text{ }\mu\text{s}$, $f_{RF} = 97.1\text{ MHz}$; unless otherwise specified.

AM condition: all RF voltages are RMS values measured at the input of a $15\text{ pF}/60\text{ pF}$ dummy aerial; $f_{mod} = 400\text{ Hz}$, $m = 30\%$, $f_{RF} = 990\text{ kHz}$; unless otherwise specified.

All values measured in a test circuit according to [Figure 29](#); default settings; audio signals measured at LOUT and ROUT with IEC tuner filter (200 Hz to 15 kHz; IEC 60315-4); unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Audio part; pin MPXIN						
R_i	input resistance	data byte 3h bit LOCUT = 0 (FM or AM)	-	220	-	$\text{k}\Omega$
		data byte 3h bit LOCUT = 1 (AM)	-	16	-	$\text{k}\Omega$
$\alpha_{\text{bal(ch)}}$	channel balance	balance between R and L channel	-1	-	+1	dB
$\alpha_{\text{sup(pilot)}}$	pilot suppression	9 % pilot; $f_{\text{pilot}} = 19\text{ kHz}$; referenced to 91 % FM modulation	30	40	-	dB
m_{pilot}	modulation degree of pilot tone	threshold for pilot detection				
		stereo on	2	3.9	5.8	%
		stereo off	1.2	3.1	5	%
$\alpha_{\text{hys(pilot)}}$	pilot hysteresis		0.7	0.8	1.6	%
$t_{\text{det(pilot)}}$	pilot detection time		-	30	100	ms
Audio output; pins LOUT and ROUT						
V_o	output voltage	$\Delta f = 22.5\text{ kHz}$; $f_{\text{AF}} = 1\text{ kHz}$				
		data byte 3h bit OUTA = 1	200	290	410	mV
		data byte 3h bit OUTA = 0	80	120	175	mV
α_{AF}	AF attenuation	mono; pre-emphasis = $50\text{ }\mu\text{s}$; referenced to $f_{\text{AF}} = 1\text{ kHz}$				
		$f_{\text{AF}} = 50\text{ Hz}$	-0.6	-0.1	+0.4	dB
		$f_{\text{AF}} = 15\text{ kHz}$	-1.5	0	+1.5	dB
α_{cs}	channel separation	$V_{i(\text{RF})} = 1\text{ mV}$; data byte Fh bits CHSEP[2:0] = 100	26	40	-	dB
THD	total harmonic distortion	mono; $\Delta f = 75\text{ kHz}$; $V_{i(\text{RF})} = 1\text{ mV}$	-	0.4	0.8	%
		stereo; $\Delta f = 67.5\text{ kHz}$; L or R	-	-	1	%
R_L	load resistance		10	-	-	$\text{k}\Omega$
C_L	load capacitance		-	-	20	pF
FM noise blanker						
(S+N)/N	signal plus noise-to-noise ratio	noise pulses at RF input signal $t_p = 5\text{ ns}$; $t_r < 1\text{ ns}$; $t_f < 1\text{ ns}$; $f_p = 100\text{ Hz}$; $V_p = 500\text{ mV}$; $V_{i(\text{RF})} = 40\text{ dB}\mu\text{V}$; quasi peak; audio filter according "ITU-R BS.468-4"	-	30	-	dB
AM path						
$V_{i(\text{sens})}$	input sensitivity voltage	S/N = 26 dB; data byte 3h bits DEMP[1:0] = 10				
		MW	-	34	-	$\text{dB}\mu\text{V}$
		LW	-	40	-	$\text{dB}\mu\text{V}$
$V_{n(i)(\text{eq})}$	equivalent input noise voltage	$C_{\text{source}} = 100\text{ pF}$	-	1	-	$\text{nV}/\sqrt{\text{Hz}}$

Table 60. Dynamic characteristics ...continued

$V_{CC} = 8.5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

FM condition: all RF voltages refer to an unterminated RMS voltage with a source impedance $75\text{ }\Omega$; $f_{mod} = 1\text{ kHz}$,

$\Delta f = 22.5\text{ kHz}$, de-emphasis = $50\text{ }\mu\text{s}$, $f_{RF} = 97.1\text{ MHz}$; unless otherwise specified.

AM condition: all RF voltages are RMS values measured at the input of a $15\text{ pF}/60\text{ pF}$ dummy aerial; $f_{mod} = 400\text{ Hz}$,

$m = 30\%$, $f_{RF} = 990\text{ kHz}$; unless otherwise specified.

All values measured in a test circuit according to [Figure 29](#); default settings; audio signals measured at LOUT and ROUT with IEC tuner filter (200 Hz to 15 kHz; IEC 60315-4); unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
(S+N)/N	signal plus noise-to-noise ratio	$V_{i(RF)} = 10\text{ mV}$	50	56	-	dB
f_{IF}	IF frequency		-	25	-	kHz
α_{image}	image rejection	$f_{RF(image)} = f_{RF(wanted)} \pm 2 \times f_{IF}$	40	55	-	dB
$B_{filtr(IF)}$	IF filter bandwidth	-3 dB bandwidth	5	6.5	8	kHz
S_{stat}	static selectivity	$f_{tune} \pm 10\text{ kHz}$	40	48	-	dB
		$f_{tune} \pm 20\text{ kHz}$	65	78	-	dB
$V_{i(RF)(max)}$	maximum RF input voltage	THD = 10 %; $m = 80\%$; active antenna $50\text{ }\Omega$	120	135	-	$\text{dB}\mu\text{V}$
IP2	second-order intercept point		150	170	-	$\text{dB}\mu\text{V}$
IP3	third-order intercept point	$\Delta f = 40\text{ kHz}$	116	127	-	$\text{dB}\mu\text{V}$
AM LNA and AM RF AGC; input pins AMRFIN and AMRFDEC						
R_i	input resistance	$f_{RF} = 990\text{ kHz}$	-	20	-	Ω
C_i	input capacitance	AGC maximum gain	[1][2]	530	-	pF
MW band with passive antenna (measured with dummy aerial 15 pF/60 pF)						
$V_{i(RF)AGC}$	AGC RF input voltage	switched LNA AGC: $V_{i(RF)}$ value, at which the LNA gain decreases with increasing $V_{i(RF)}$; $m = 0\%$; start of AGC; first step	110	113	116	$\text{dB}\mu\text{V}$
$V_{i(RF)AGC(hys)}$	hysteresis of AGC RF input voltage	hysteresis of AGC start	1	4	7	dB
MW band with active antenna (measured with dummy aerial 50 Ω)						
$V_{i(RF)AGC}$	AGC RF input voltage	switched LNA AGC: $V_{i(RF)}$ value, at which the LNA gain decreases with increasing $V_{i(RF)}$; $m = 0\%$; start of AGC; first step	78	81	84	$\text{dB}\mu\text{V}$
$V_{i(RF)AGC(hys)}$	hysteresis of AGC RF input voltage	hysteresis of AGC start	1	3	6	dB
LW band with passive antenna (measured with dummy aerial 15 pF/60 pF)						
$V_{i(RF)AGC}$	AGC RF input voltage	switched LNA AGC: $V_{i(RF)}$ value, at which the LNA gain decreases with increasing $V_{i(RF)}$; $f_{RF} = 207\text{ kHz}$; $m = 0\%$; start of AGC; first step	-	104	-	$\text{dB}\mu\text{V}$
$V_{i(RF)AGC(hys)}$	hysteresis of AGC RF input voltage	hysteresis of AGC start	1	4	7	dB

Table 60. Dynamic characteristics ...continued

$V_{CC} = 8.5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

FM condition: all RF voltages refer to an unterminated RMS voltage with a source impedance $75\text{ }\Omega$; $f_{mod} = 1\text{ kHz}$, $\Delta f = 22.5\text{ kHz}$, de-emphasis = $50\text{ }\mu\text{s}$, $f_{RF} = 97.1\text{ MHz}$; unless otherwise specified.

AM condition: all RF voltages are RMS values measured at the input of a $15\text{ pF}/60\text{ pF}$ dummy aerial; $f_{mod} = 400\text{ Hz}$, $m = 30\%$, $f_{RF} = 990\text{ kHz}$; unless otherwise specified.

All values measured in a test circuit according to [Figure 29](#); default settings; audio signals measured at LOUT and ROUT with IEC tuner filter (200 Hz to 15 kHz; IEC 60315-4); unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<i>LW band with active antenna (measured with dummy aerial $50\text{ }\Omega$)</i>						
$V_{i(RF)AGC}$	AGC RF input voltage	switched LNA AGC: $V_{i(RF)}$ value, at which the LNA gain decreases with increasing $V_{i(RF)}$; $f_{RF} = 207\text{ kHz}$; $m = 0\%$; start of AGC; first step	-	80	-	$\text{dB}\mu\text{V}$
$V_{i(RF)AGC(hys)}$	hysteresis of AGC RF input voltage	hysteresis of AGC start	1	4	7	dB
Continuous AM RF AGC						
$V_{i(RF)AGC}$	AGC RF input voltage	linear RF AGC: $V_{i(RF)}$ at which AGC starts; $m = 0\%$				
		data byte 2h bits RFAGC[1:0] = 00	87	90	93	$\text{dB}\mu\text{V}$
		data byte 2h bits RFAGC[1:0] = 01	85	88	91	$\text{dB}\mu\text{V}$
		data byte 2h bits RFAGC[1:0] = 10	83	86	89	$\text{dB}\mu\text{V}$
		data byte 2h bits RFAGC[1:0] = 11	81	84	87	$\text{dB}\mu\text{V}$
t_s	settling time	$V_{i(RF)} = 10\text{ mV}$ to 600 mV	-	64	-	ms
		$V_{i(RF)} = 600\text{ mV}$ to 10 mV	-	3.2	-	s
$I_{source(AGC)}$	AGC source current	AGC attack; $V_{i(RF)M} = 105\text{ dB}\mu\text{V}$ (peak); normal mode	25	35	50	μA
		AGC attack; fast mode after tuning and AGC switching	0.7	1	1.4	mA
$I_{sink(AGC)}$	AGC sink current	AGC release; normal mode	0.7	1	1.4	μA
		AGC release; fast mode after tuning and AGC switching	17.5	25	35	μA
Continuous IF AGC 1						
$V_{i(RF)AGC}$	AGC RF input voltage	linear IF AGC 1: $V_{i(RF)}$ at which AGC starts; $m = 0\%$	59	62	65	$\text{dB}\mu\text{V}$
$I_{source(AGC)}$	AGC source current	AGC attack; $V_{i(RF)M} = 80\text{ dB}\mu\text{V}$ (peak); normal mode	35	50	70	μA
		AGC attack; fast mode after tuning and AGC switching	0.875	1.25	1.75	mA
$I_{sink(AGC)}$	AGC sink current	AGC release; normal mode	0.7	1	1.4	μA
		AGC release; fast mode after tuning and AGC switching	17.5	25	35	μA
Continuous IF AGC 2						
$V_{i(RF)AGC}$	AGC RF input voltage	linear IF AGC 2: $V_{i(RF)}$ at which AGC starts; $m = 0\%$	19	22	25	$\text{dB}\mu\text{V}$
$I_{source(AGC)}$	AGC source current	AGC attack; $V_{i(RF)M} = 50\text{ dB}\mu\text{V}$ (peak); normal mode	4	6	8	μA
		AGC attack; fast mode after tuning and AGC switching	100	150	200	μA

Table 60. Dynamic characteristics ...continued

$V_{CC} = 8.5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

FM condition: all RF voltages refer to an unterminated RMS voltage with a source impedance $75\ \Omega$; $f_{mod} = 1\text{ kHz}$, $\Delta f = 22.5\text{ kHz}$, de-emphasis = $50\ \mu\text{s}$, $f_{RF} = 97.1\text{ MHz}$; unless otherwise specified.

AM condition: all RF voltages are RMS values measured at the input of a $15\text{ pF}/60\text{ pF}$ dummy aerial; $f_{mod} = 400\text{ Hz}$, $m = 30\%$, $f_{RF} = 990\text{ kHz}$; unless otherwise specified.

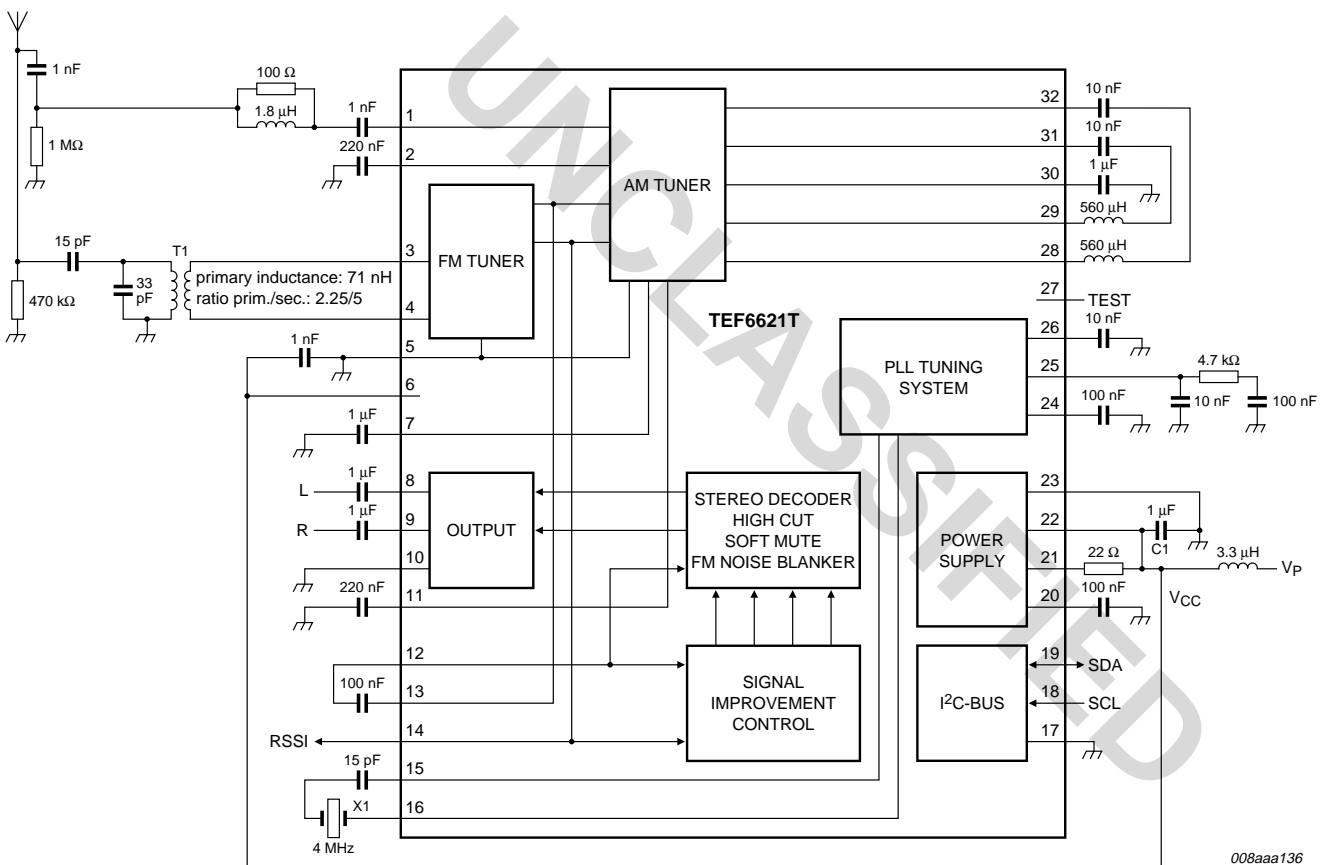
All values measured in a test circuit according to [Figure 29](#); default settings; audio signals measured at LOUT and ROUT with IEC tuner filter (200 Hz to 15 kHz; IEC 60315-4); unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{\text{sink(AGC)}}$	AGC sink current	AGC release; normal mode	0.7	1	1.4	μA
		AGC release; fast mode after tuning and AGC switching	17.5	25	35	μA
AM demodulator; pin MPXOUT						
V_o	output voltage	$m = 30\%$	175	210	250	mV
Audio output; pins LOUT and ROUT						
V_o	output voltage	$m = 30\%$; $f_{AF} = 400\text{ Hz}$; data byte 3h bits DEMP[1:0] = 10				
		data byte 3h bit OUTA = 1	200	270	355	mV
		data byte 3h bit OUTA = 0	85	115	150	mV
α_{AF}	AF attenuation	referenced to $f_{AF} = 400\text{ Hz}$; 210 mV input at pin MPXIN				
		$f_{AF} = 100\text{ Hz}$; data byte 3h bit LOCUT = 1	-4.5	-3	-1.5	dB
		$f_{AF} = 1.5\text{ kHz}$; data byte 3h bits DEMP[1:0] = 10	-4.5	-3	-2	dB
		$f_{AF} = 5\text{ kHz}$; data byte 3h bits DEMP[1:0] = 10	-24	-21	-18	dB
THD	total harmonic distortion	$V_{i(RF)} = 1\text{ mV}$; $m = 80\%$	-	0.7	1	%
α_{ripple}	ripple rejection	$V_{\text{ripple}} / V_{\text{audio}}$; $V_{\text{ripple}} = 100\text{ mV}$; $f_{\text{ripple}} = 100\text{ Hz}$	30	37	-	dB
AM RSSI; pin RSSI						
V_{RSSI}	RSSI voltage	$V_{i(RF)} = -20\text{ dB}\mu\text{V}$ at dummy aerial input	0.9	1.1	1.25	V
		$V_{i(RF)} = 14\text{ dB}\mu\text{V}$ at dummy aerial input	1.6	1.9	2.2	V
		$V_{i(RF)} = 34\text{ dB}\mu\text{V}$ at dummy aerial input	2.6	2.9	3.2	V
$\Delta V_{\text{RSSI}}/\Delta L_{i(RF)}$	RSSI voltage difference to RF input level difference ratio	$5\ \mu\text{V} < V_{i(RF)} < 50\ \mu\text{V}$	45	50	55	mV/dB
AM IF counter						
$f_{\text{IFc(res)}}$	IF counter frequency resolution		-	500	-	Hz

[1] The switched input capacitance is part of the switched RF AGC function.

[2] The input impedance of the AM LNA depends on the AGC state.

13. Application information



008aaa136

For list of components see [Table 61](#) and for crystal specification see [Table 62](#).

Fig 27. Application diagram of TEF6621T

13.1 Printed-circuit board

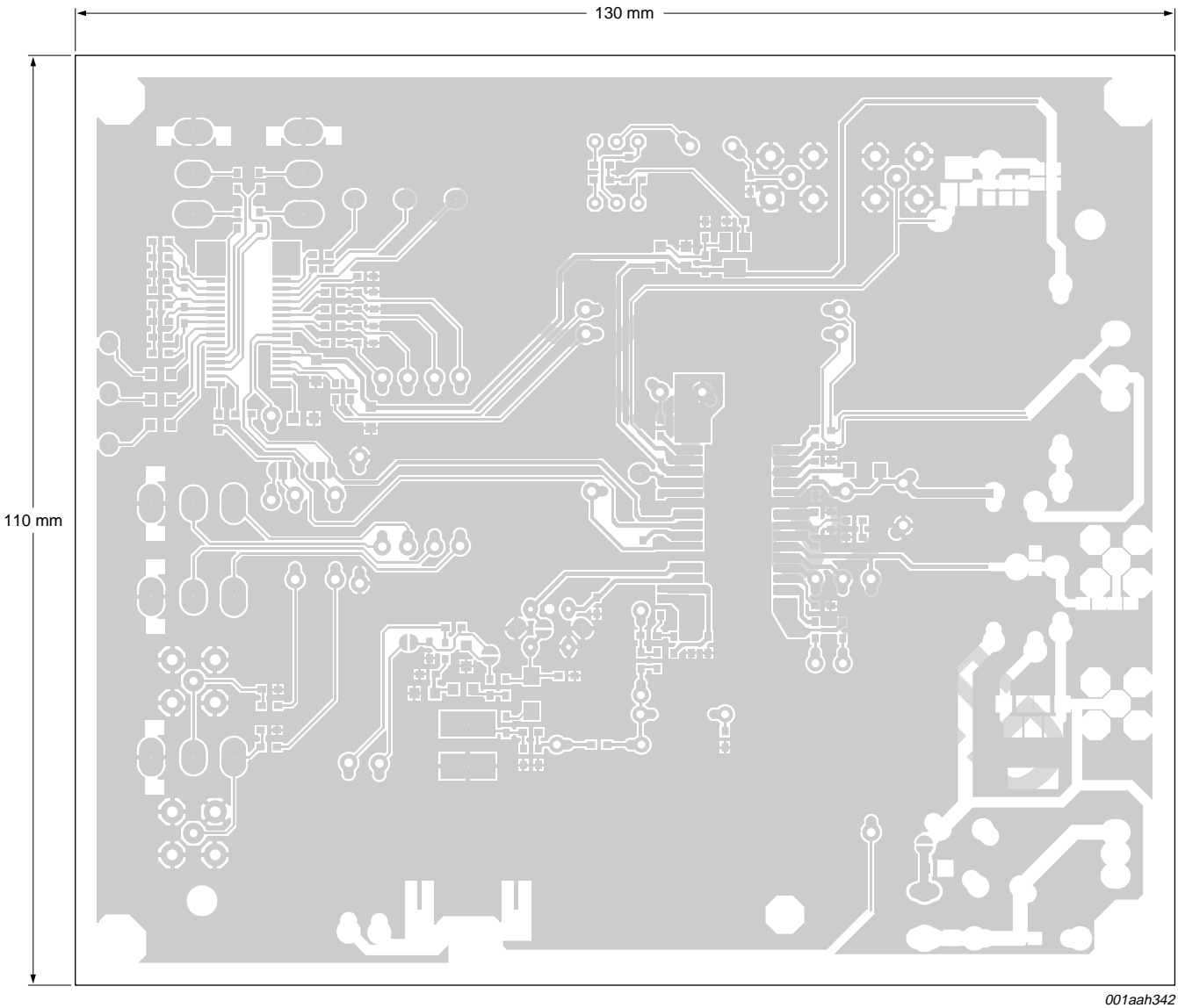
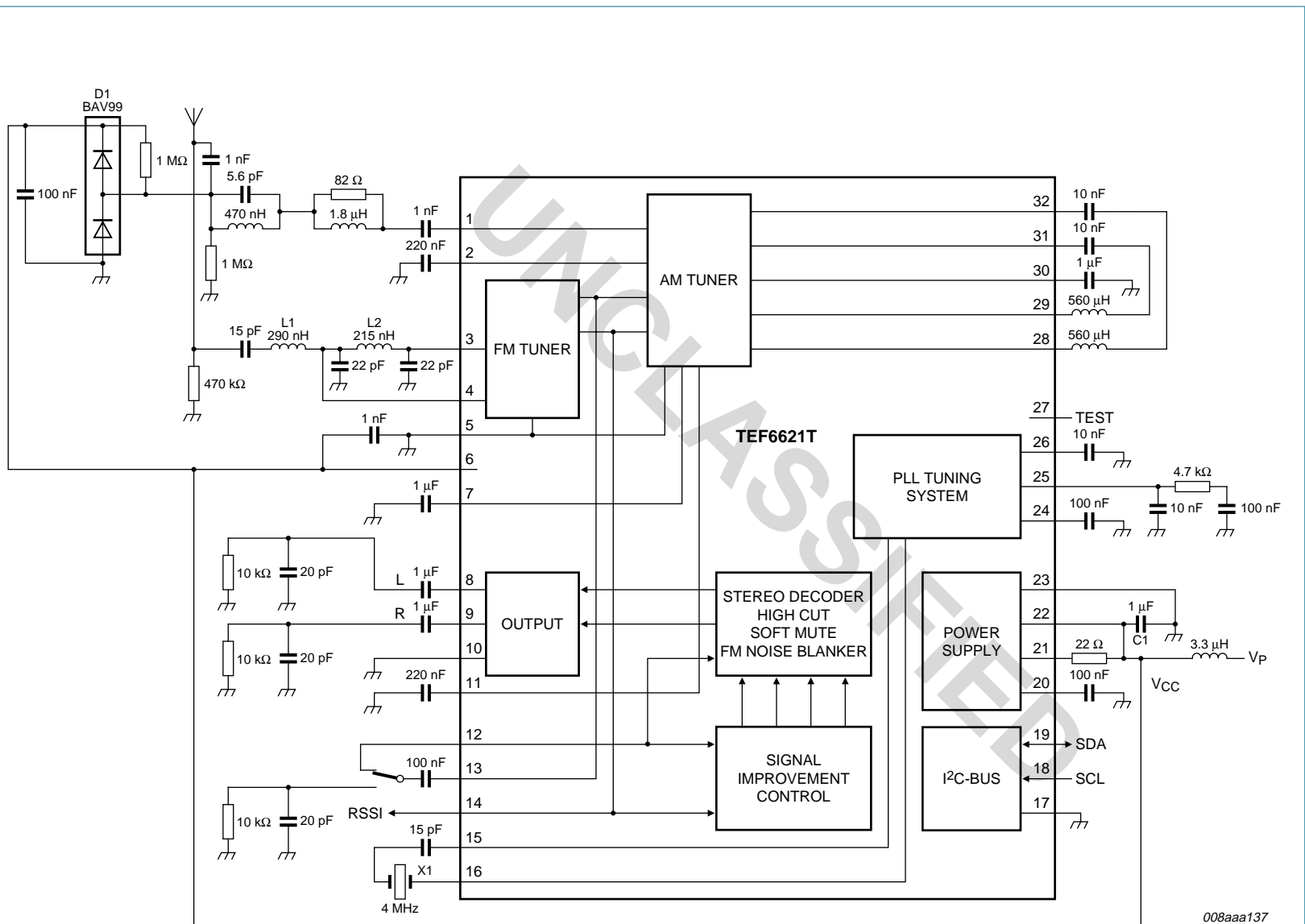


Fig 28. Printed-circuit board layout, suggested for application (this layout has been used in the NXP GH989 reference design, 35 μ m)

14. Test information



008aaa137

For list of components see [Table 61](#) and for crystal specification see [Table 62](#).

Fig 29. Test circuit of TEF6621T

Table 61. List of components for Figure 27 and Figure 29

Symbol	Component	Type	Manufacturer
C1	decoupling capacitor	1 μ F; X7R 0805	any
D1	ESD protection diode	BAV99	NXP Semiconductors
L1	FM RF input 1	290 nH; LQH31HNR29K03L	Murata
L2	FM RF input 2	215 nH; LQH31HNR21K01L	Murata
T1	transformer	#P600ENS-10959QH	TOKO
X1	crystal 4 MHz	LN-G102-1413	NDK

Table 62. 4 MHz crystal specification for Figure 27 and Figure 29

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{xtal}	crystal frequency	fundamental frequency	-	4.000	-	MHz
C_L	load capacitance		-	18	-	pF
C_{shunt}	shunt capacitance		-	-	7	pF
C_1	motional capacitance		-	10	-	fF
R_s	series resistance		-	-	150	Ω
$\Delta f_{\text{xtal}}/f_{\text{xtal}}$	relative crystal frequency variation	at 25 °C	-25	-	+25	10^{-6}
		caused by ageing	-5	-	+5	10^{-6}
		caused by temperature	-30	-	+30	10^{-6}
T_{amb}	ambient temperature		-20	-	+85	°C

Table 63. DC operating points

$V_{CC2} = 8.5\text{ V}$; $V_{CC1} = 8.5\text{ V}$; $V_{i(RF)} = 0\ \mu\text{V}$; audio output gain low; unless otherwise specified.

Symbol	Pin	Unloaded DC voltage (V)					
		AM mode			FM mode		
		Min	Typ	Max	Min	Typ	Max
AMRFIN	1	-	2.85	-	-	-	-
AMRFDEC	2	-	4.1	-	-	-	-
FMIN2	3	-	-	-	-	3.1	-
FMIN1	4	-	-	-	-	3.1	-
GNDRF	5	external GND			external GND		
V_{CC2}	6	external 8.5			external 8.5		
AMRFAGC	7	-	1.8	-	-	-	-
LOUT	8	-	3.8	-	-	3.8	-
ROUT	9	-	3.8	-	-	3.8	-
GNDAUD	10	external GND			external GND		
AMIFAGC2	11	-	-	-	-	-	-
MPXIN	12	-	3.7	-	-	3.7	-
MPXOUT	13	-	4	-	-	4	-
RSSI	14	-	1.2	-	-	0.8	-
XTAL2	15	-	6.5	-	-	6.5	-
XTAL1	16	-	6.5	-	-	6.5	-
GND D	17	external GND			external GND		
SCL	18	external I ² C-bus voltage			external I ² C-bus voltage		
SDA	19	external I ² C-bus voltage			external I ² C-bus voltage		
VREF	20	3.9	4.0	4.1	3.9	4.0	4.1
VREGSUP	21	5.6	6.5	7	5.6	6.5	7
V_{CC1}	22	external 8.5			external 8.5		
GND	23	external GND			external GND		
VCODEC	24	-	5.7	-	-	5.7	-
PLL	25	1.2	-	5.5	1.2	-	5.5
PLLREF	26	-	2.25	-	-	2.25	-
TEST	27	-	-	-	-	-	-
AMSELIN1	28	1.2	1.55	1.9	-	-	-
AMSELIN2	29	1.2	1.55	1.9	-	-	-
AMIFAGC1	30	-	5.5	-	-	-	-
AMSELOUT1	31	6.5	6.8	7.15	-	-	-
AMSELOUT2	32	6.5	6.8	7.15	-	-	-

15. Package outline

SO32: plastic small outline package; 32 leads; body width 7.5 mm

SOT287-1

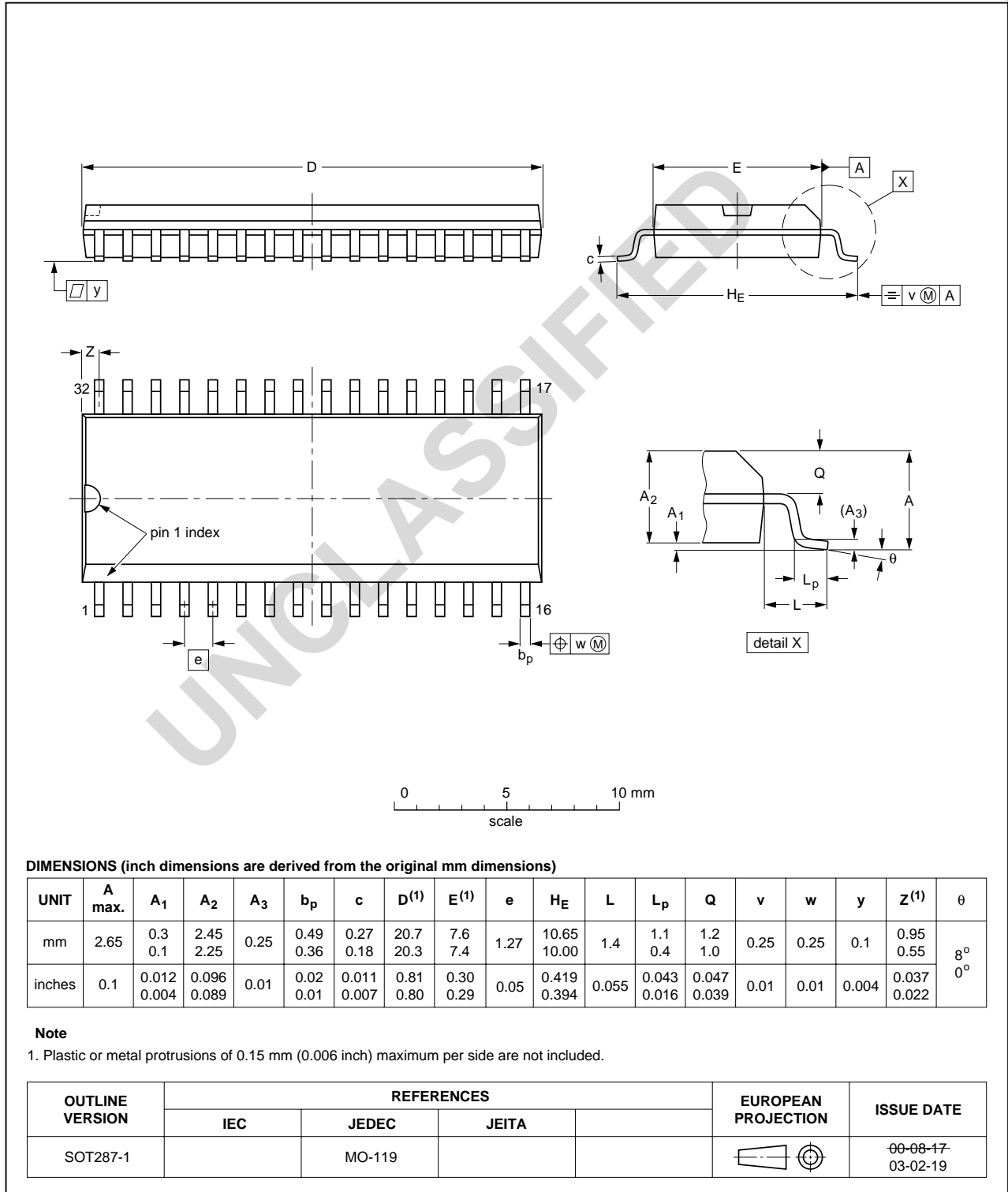


Fig 30. Package outline SOT287-1 (SO32)

16. Soldering of SMD packages

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365 "Surface mount reflow soldering description"*.

16.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

16.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- Board specifications, including the board finish, solder masks and vias
- Package footprints, including solder thieves and orientation
- The moisture sensitivity level of the packages
- Package placement
- Inspection and repair
- Lead-free soldering versus SnPb soldering

16.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- Solder bath specifications, including temperature and impurities

16.4 Reflow soldering

Key characteristics in reflow soldering are:

- Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see [Figure 31](#)) than a SnPb process, thus reducing the process window
- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board
- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with [Table 64](#) and [65](#)

Table 64. SnPb eutectic process (from J-STD-020C)

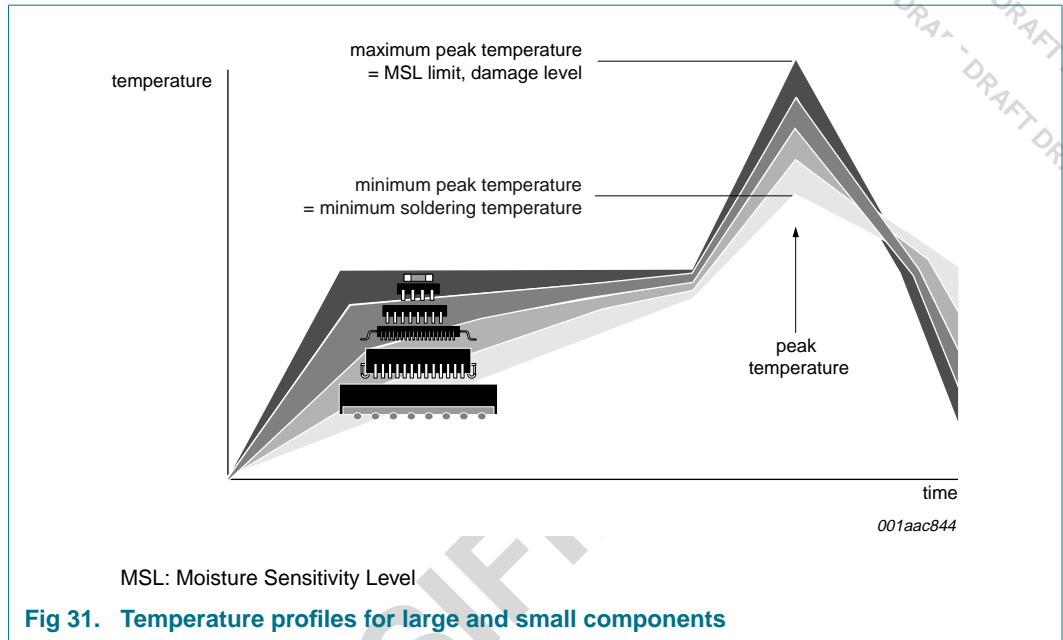
Package thickness (mm)	Package reflow temperature (°C)	
	Volume (mm ³)	
	< 350	≥ 350
< 2.5	235	220
≥ 2.5	220	220

Table 65. Lead-free process (from J-STD-020C)

Package thickness (mm)	Package reflow temperature (°C)		
	Volume (mm ³)		
	< 350	350 to 2000	> 2000
< 1.6	260	260	260
1.6 to 2.5	260	250	245
> 2.5	250	245	245

Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

Studies have shown that small packages reach higher temperatures during reflow soldering, see [Figure 31](#).



For further information on temperature profiles, refer to Application Note AN10365 “Surface mount reflow soldering description”.

17. Abbreviations

Table 66. Abbreviations

Acronym	Description
AGC	Automatic Gain Control
HCC	High-Cut Control
I ² C-bus	Inter IC bus
IF	Intermediate Frequency
LO	Local Oscillator
LW	Long Wave
MPX	Multiplex
MW	Medium Wave
PLL	Phase-Locked Loop
RF	Radio Frequency
RSSI	Received Signal Strength Indication
USN	UltraSonic Noise
VCO	Voltage-Controlled Oscillator
WAM	Wideband AM

18. Revision history

Table 67. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
TEF6621_1	yyyymmdd	Objective data sheet	-	-

UNCLASSIFIED

19. Legal information

19.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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21. Contents

1	General description	1	13.1	Printed-circuit board	48
2	Features	1	14	Test information	49
3	Quick reference data	2	15	Package outline	52
4	Ordering information	2	16	Soldering of SMD packages	53
5	Block diagram	3	16.1	Introduction to soldering	53
6	Pinning information	4	16.2	Wave and reflow soldering	53
6.1	Pinning	4	16.3	Wave soldering	53
6.2	Pin description	4	16.4	Reflow soldering	54
7	Functional description	5	17	Abbreviations	55
7.1	FM tuner	5	18	Revision history	56
7.2	AM tuner	5	19	Legal information	57
7.3	PLL tuning system	5	19.1	Data sheet status	57
7.4	FM stereo decoder	5	19.2	Definitions	57
7.5	Weak signal processing and noise blanker	5	19.3	Disclaimers	57
7.6	I ² C-bus transceiver	6	19.4	Trademarks	57
8	I²C-bus protocol	6	20	Contact information	57
8.1	Read mode	6	21	Contents	58
8.1.1	Read mode: data byte STATUS	7			
8.1.2	Read mode: data byte LEVEL	7			
8.1.3	Read mode: data byte USN_WAM	8			
8.1.4	Read mode: data byte IFCOUNTER	8			
8.2	Write mode	9			
8.2.1	Mode and subaddress byte for write	10			
8.2.2	Write mode: data byte TUNER0	22			
8.2.3	Write mode: data byte TUNER1	22			
8.2.4	Write mode: data byte TUNER2	23			
8.2.5	Write mode: data byte RADIO	24			
8.2.6	Write mode: data byte SOFTMUTE0	24			
8.2.7	Write mode: data byte SOFTMUTE1	25			
8.2.8	Write mode: data byte SOFTMUTE2_FM	27			
8.2.9	Write mode: data byte SOFTMUTE2_AM	29			
8.2.10	Write mode: data byte HIGHCUT0	29			
8.2.11	Write mode: data byte HIGHCUT1	30			
8.2.12	Write mode: data byte HIGHCUT2	32			
8.2.13	Write mode: data byte STEREO0	34			
8.2.14	Write mode: data byte STEREO1	34			
8.2.15	Write mode: data byte STEREO2	36			
8.2.16	Write mode: data byte CONTROL	37			
8.2.17	Write mode: data byte LEVEL_OFFSET	38			
8.2.18	Write mode: data byte AM_LNA	38			
9	Limiting values	39			
10	Thermal characteristics	39			
11	Static characteristics	40			
12	Dynamic characteristics	40			
13	Application information	47			

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